WHAT IS CLAIMED IS:

1. A liquid crystal display device, comprising:

an active matrix substrate;

a counter substrate; and

a liquid crystal layer interposed between the active matrix substrate and the counter substrate,

wherein the active matrix substrate includes:

a plate;

a thin film transistor provided on the plate; and

a side light shielding layer for covering at least a portion of a side surface of the thin film transistor.

2. A liquid crystal display device according to claim 1, wherein:

the active matrix substrate further includes a semiconductor layer, and

the thin film transistor includes a part of the semiconductor layer.

3. A liquid crystal display device according to claim 1, wherein:

the thin film transistor includes a gate electrode, a source electrode, and a drain electrode, and

the active matrix substrate further includes a pixel electrode, a gate line acting as the gate electrode of the thin film transistor, and a signal line connected to the source electrode of the thin film transistor.

4. A liquid crystal display device according to claim 2, wherein:

the active matrix substrate further includes an insulating layer provided on the plate and having a stepped portion having a side wall substantially perpendicular to the plate;

the semiconductor layer is provided on the stepped portion of the insulating layer; and

the side light shielding layer is provided along the side wall of the stepped portion of the insulating layer.

5. A liquid crystal display device according to claim 1, wherein the active matrix substrate further includes a lower light shielding layer provided below the thin film transistor.

6. A liquid crystal display device according to claim 5, wherein the side light shielding layer is in contact with

the lower light shielding layer.

7. A liquid crystal display device according to claim 1, wherein the active matrix substrate further includes an upper light shielding layer provided on the thin film transistor.

8. A liquid crystal display device according to claim 3, wherein the side light shielding layer is provided so as to cover a side surface of the gate line.

9. A liquid crystal display device according to claim 3, wherein the side light shielding layer is provided so as to cover a side surface of the signal line.

10. A liquid crystal display device according to claim 5, wherein the active matrix substrate further includes an additional capacitance electrode.

11. A liquid crystal display device according to claim 10, wherein the additional capacitance electrode is provided below the lower light shielding layer.

12. A liquid crystal display device according to claim 10,

wherein the additional capacitance electrode is provided between the lower light shielding layer and the thin film transistor.

13. A liquid crystal display device according to claim 10, wherein the additional capacitance electrode is connected to the thin film transistor.

14. A liquid crystal display device according to claim 10, wherein the side light shielding layer is in contact with the additional capacitance electrode.

15. A liquid crystal display device according to claim 1, wherein the thin film transistor has an LDD structure.

16. A liquid crystal display device according to claim 1, wherein the side light shielding layer is formed of polycrystalline silicon.

17. A liquid crystal display device according to claim 1, wherein the side light shielding layer is formed of metal or metal silicide.

18. A liquid crystal display device according to claim 1,

wherein the side light shielding layer has a two-component structure including metal or metal silicide and polycrystalline silicon.

19. A method for producing a liquid crystal display device including an active matrix substrate, a counter substrate, and a liquid crystal layer interposed between the active matrix substrate and the counter substrate, the method comprising the steps of:

forming a thin film transistor on a plate of the active matrix substrate; and

forming a side light shielding layer for covering at least a portion of a side surface of the thin film transistor.

20. A method according to claim 19, wherein the step of forming the thin film transistor includes the step of forming a semiconductor layer used as a part of the thin film transistor.

21. A method according to claim 20, further comprising the step of forming a first insulating layer on the plate, the first insulating layer having a stepped portion having a side wall substantially perpendicular to the plate,

wherein:

the step of forming the semiconductor layer includes the step of forming the semiconductor layer on the stepped portion of the first insulating layer, and

the step of forming the side light shielding layer includes the step of forming the side light shielding layer along the side wall of the stepped portion of the first insulating layer.

22. A method according to claim 21, wherein the step of forming the side light shielding layer includes the steps of forming a layer of a material of the side light shielding layer so as to cover the stepped portion of the first insulating layer, and partially removing the layer by dry etching.

23. A method according to claim 21, further comprising the steps of forming a second insulating layer on the semiconductor layer, and flattening a surface of the second insulating layer before the stepped portion of the first insulating layer is formed.

24. A method according to claim 23, wherein the step of flattening the surface of the second insulating layer

includes the step of flattening the second insulating layer by chemical mechanical polishing.